# LM148 Low Power Quad 741 Operational Amplifier

### Features

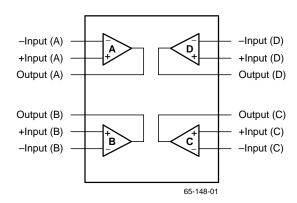
- 741 op amp operating characteristics
- Low supply current drain—0.6 mA/amplifier
- Class AB output stage—no crossover distortion
- Pin compatible with the LM124
- Low input offset voltage-1.0 mV
- Low input offset current—4.0 nA
- Low input bias current—30 nA
- Unity gain bandwidth—1.0 MHz
- Channel Separation—120 dB
- Input and output overload protection

### Description

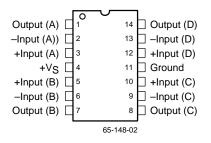
The LM148 is a true quad 741. It consists of four independent high-gain, internally compensated, low-power operational amplifiers which have been designed to provide functional characteristics identical to those of the familiar 741 operational amplifier. In addition, the total supply current for all four amplifiers is comparable to the supply current of a single 741 type op amp. Other features include input offset currents and input bias currents which are much less than those of a standard 741. Also, excellent isolation between amplifiers has been achieved by independently biasing each amplifier and using layout techniques which minimize thermal coupling.

The LM148 can be used anywhere multiple 741 type amplifiers are being used and in applications where amplifier matching or high packing density is required.

# **Block Diagram**



# **Pin Assignments**



# **Absolute Maximum Ratings**

Parameter	Min.	Max.	Unit	
Supply Voltage	-22	+22	V	
Differential Input Voltage		44	V	
Input Voltage <sup>1</sup>	-22	+22	V	
Output Short Circuit Duration <sup>2</sup>		Indefinite		
Storage Temperature Range	-65	+150	°C	
Operating Temperature Range	-55	+125	°C	
Lead Soldering Temperature (60 sec.)	+300°C			

Notes:

1. For supply voltages less than ±15V, the absolute maximum input voltage is equal to the supply voltage.

2. Short circuit to ground on one amplifier only.

# **Thermal Characteristics**

Parameter	14-Lead Ceramic DIP		
Maximum Junction Temperature	+175°C		
Maximum PD TA < 50°C	1042 mW		
Thermal Resistance, $\theta_{JC}$	60°C/W		
Thermal Resistance, θJA	120°C/W		
For T <sub>A</sub> > 50°C derate at	8.33 mW/°C		

### **Electrical Characteristics**

(Vs =  $\pm 15V$  and TA =  $25^{\circ}C$ , unless otherwise noted)

Parameter	Test Conditions		Min.	Тур.	Max.	Unit
Input Offset Voltage	Rs ≤ 10KΩ			1.0	5.0	mV
Input Offset Current				4.0	25	nA
Input Bias Current	-			30	100	nA
Input Resistance (Differential Mode) <sup>1</sup>			0.8	2.5		MΩ
Supply Current, All Amplifiers	Vs = ±15V			2.4	3.6	mA
Large Signal Voltage Gain	$V_{S} = \pm 15V, V_{OUT} = \pm 10V,$ $R_{L} \ge 2K\Omega$		50	160		V/mV
Channel Separation	F = 1 Hz 20 KHz			120		dB
Unity Gain Bandwidth				1.0		MHz
Phase Margin					60	Degrees
Slew Rate					0.5	V/µS
Short Circuit Current				25		mA
The following specifications apply for	or Vs = ±15V, -55	°C ≤ TA ≤ +125°	C.			•
Input Offset Voltage	$R_S \le 10 K\Omega$	$R_{S} \le 10 K\Omega$			6.0	mV
Input Offset Current					75	nA
Input Bias Current					325	nA
Large Signal Voltage Gain	$V_{S} = \pm 15V, V_{OUT} = 10V,$ $R_{L} < 2K\Omega$		25			V/mV
Output Voltage Swing	VS = ±15V	RL = 10KΩ	±12	±13		V
		$R_L = 2K\Omega$	±10	±12		1
Input Voltage Range	Vs = ±15V		±12			V
Common Mode Rejection Ratio	$R_{S} \le 10 K\Omega$		70	90		dB
Power Supply Rejection Ratio	$R_S \le 10 K\Omega$		77	96		dB

Note:

1. Guaranteed by design but not tested.

### **Typical Performance Characteristics**

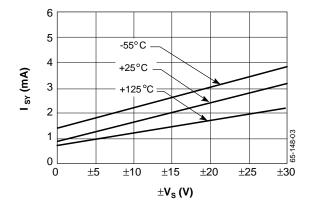


Figure 1. Supply Current vs. Supply Voltage

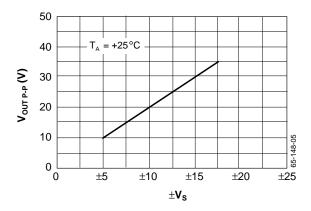


Figure 3. Output Voltage Swing vs. Supply Voltage

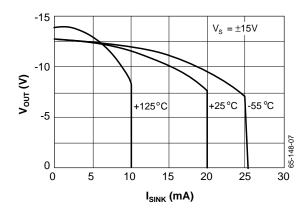


Figure 5. Negative Current Limit Output Voltage vs. Output Sink Current

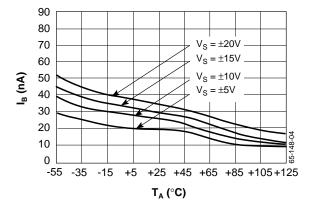


Figure 2. Input Bias Current vs. Temperature

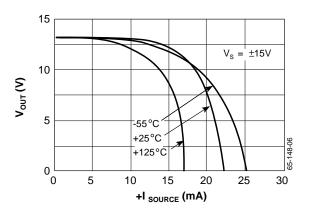


Figure 4. Positive Current Limit Output Voltage vs. Output Source Current

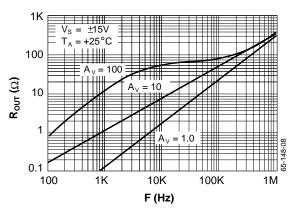
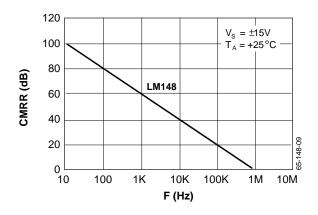


Figure 6. Output Impedance vs. Frequency

### Typical Performance Characteristics (continued)





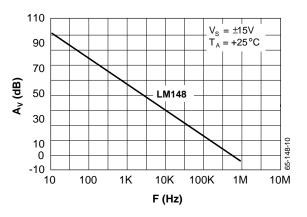


Figure 8. Open Loop Gain vs. Frequency

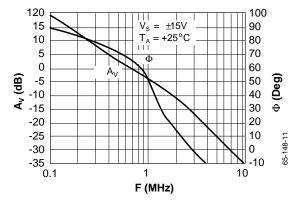
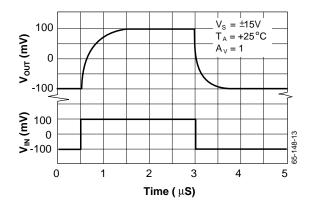


Figure 9. Gain, Phase vs. Frequency





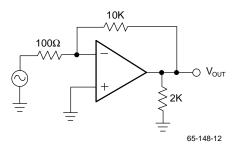


Figure 10. Gain, Phase Test Circuit

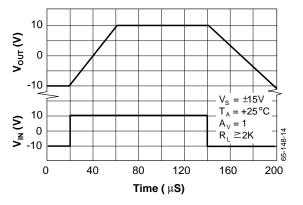
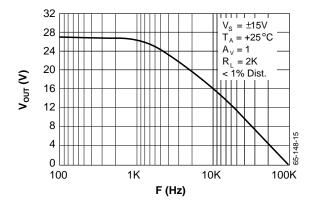


Figure 12. Large Signal Pulse Response Output Voltage vs. Time

### Typical Performance Characteristics (continued)





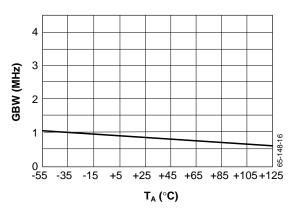


Figure 14. Gain Bandwidth Product vs. Temperature

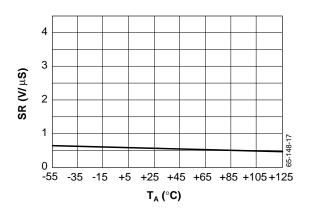
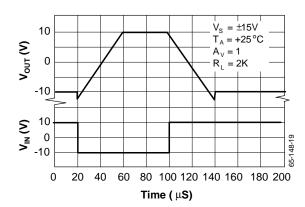


Figure 15. Slew Rate vs. Temperature





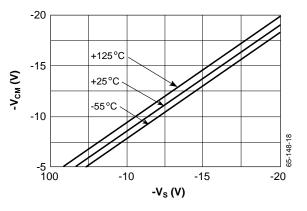


Figure 16. Negative Common Mode Input Voltage vs. Supply Voltage

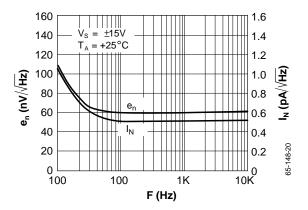


Figure 18. Input Noise Voltage, Current Densities vs. Frequency

### Typical Performance Characteristics (continued)

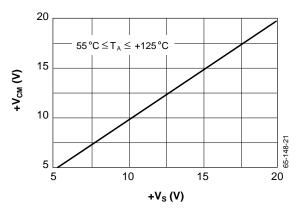


Figure 19. Positive Common Mode, Input Voltage vs. Supply Voltage

# **Typical Simulation**

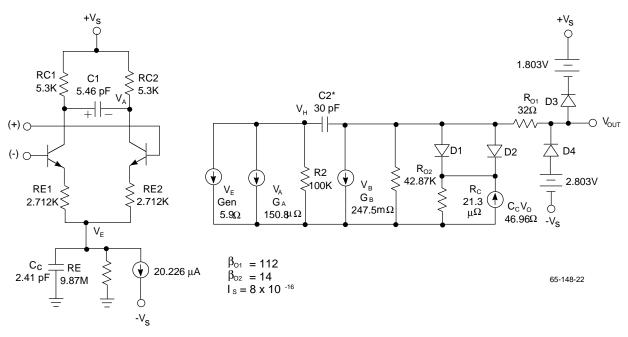


Figure 20. LM148 Macromodel for Computer Simulation

# **Applications Discussion**

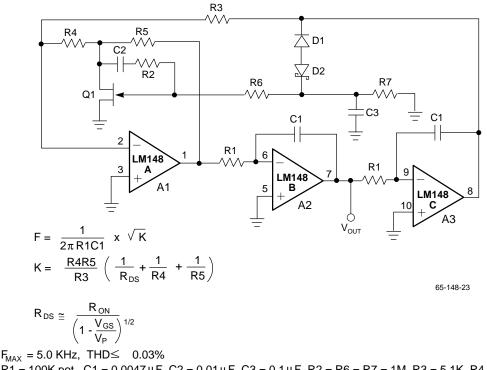
The LM148 low power quad operational amplifier exhibits performance comparable to the popular 741. Substitution can therefore be made with no change in circuit behavior.

The input characteristics of these devices allow differential voltages which exceed the supplies. Output phase will be correct as long as one of the inputs is within the operating common mode range. If both exceed the negative limit, the output will latch positive. Current limiting resistors should be used on the inputs in case voltages become excessive.

When capacitive loading becomes much greater than 100pF, a resistor should be placed between the output and feedback connection in order to reduce phase shift.

The LM148 is short circuit protected to ground and supplies continuously when only one of the four amplifiers is shorted. If multiple shorts occur simultaneously, the unit can be destroyed due to excessive power dissipation.

To assure stability and to minimize pickup, feedback resistors should be placed close to the input to maximize the feedback pole frequency (a function of input to ground capacitance). A good rule of thumb is that the feedback pole frequency should be 6 times the operating -3.0B frequency. If less, a lead capacitor should be placed between the output and input.



R1 = 100K pot., C1 =  $0.0047 \,\mu$ F, C2 =  $0.01 \,\mu$ F, C3 =  $0.1 \,\mu$ F, R2 = R6 = R7 = 1M, R3 = 5.1K, R4 =  $12\Omega$ . R5 =  $240\Omega$ , Q1 = NS5102, D1 = 1N914, D2 = 3.6V avalanche diode (ex. LM103), V<sub>S</sub> =  $\pm 15$ V A simpler version with some distortion degradation at high frequencies can be made by using A1 as a simple inverting amplifier, and by putting back to back zeners in feedback loop of A3.

Figure 21. One Decade Low Distortion Sinewave Generator

### Applications Discussion (continued)

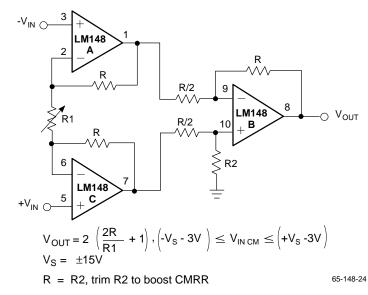


Figure 22. Low Cost Instrumentation Amplifier

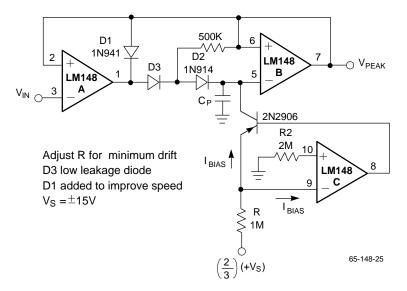
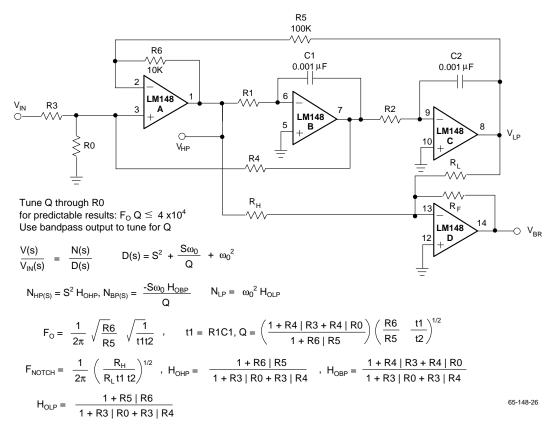
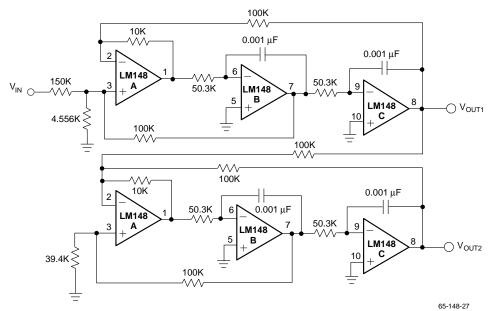


Figure 23. Low Voltage Peak Detector with Bias Current Compensation

#### Applications Discussion (continued)



#### Figure 24. Universal State-Space Filter

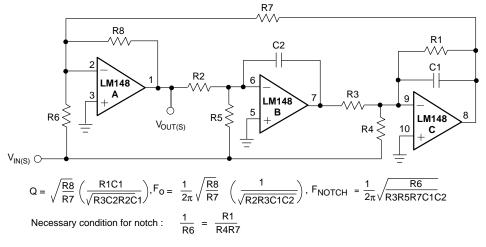


Use general equations, and tune each section separately.  $Q_{1st}$  Section = 0.541,  $Q_{2nd}$  Section = 1.306. The response should have 0 dB peaking.

#### Figure 25. 1 KHz 4-Pole Butterworth Filter

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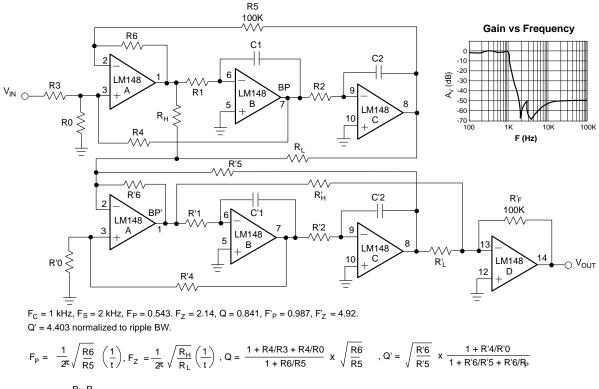
### Applications Discussion (continued)



Examples: F<sub>NOTCH</sub> = 3 kHz, Q = 5, R1 = 270K, R2 = R3 = 20K, R4 = 27K, R5 = 20K, R6 = R8 = 10K, R7 = 100K. C1 = C2 = 0.001 μF.

Better noise performance than the state-space approach.

#### Figure 26. 3 Amplifier Bi-Quad Notch Filter



 $R_{P} = \frac{R_{H}R_{L}}{R_{H} + R_{L}}$ 

Use the B'P outputs to tune Q, Q', tune the 2 sections separately. R1 = R2 = 92.6K, R3 = R4 = R5 = 100K, R6 = 10K, R0 = 107.8K, R<sub>L</sub> = 100K, R<sub>H</sub> = 155.1K, R'1 = R'2 = 50.9K, R'4 = R'5 = 100K, R'6 = 10K, R'0 = 5.78K, R'<sub>L</sub> = 100K, R'<sub>H</sub> = 248.12K, R'<sub>F</sub> = 100K.

All capacitors are 0.001µF.

Figure 27. 4th Order 1 KHz Elliptic Filter (4 Poles, 4 Zeros)

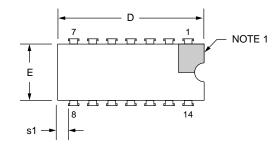
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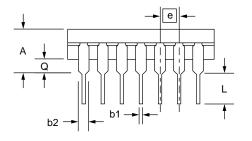
### **Mechanical Dimensions**

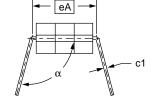
#### 14-Pin Ceramic DIP

Symbol	Inches		Millimeters		Notes
Symbol	Min.	Max.	Min.	Max.	Notes
А		.200		5.08	
b1	.014	.023	.36	.58	8
b2	.045	.065	1.14	1.65	2
c1	.008	.015	.20	.38	8
D		.785		19.94	4
E	.220	.310	5.59	7.87	4
е	.100 BSC		2.54 BSC		5, 9
eA	.300 BSC		7.62	BSC	7
L	.125	.200	3.18	5.08	
Q	.015	.060	.38	1.52	3
s1	.005	—	.13	_	6
α	90°	105°	90°	105°	

- 1. Index area: a notch or a pin one identification mark shall be located adjacent to pin one. The manufacturer's identification shall not be used as pin one identification mark.
- 2. The minimum limit for dimension "b2" may be .023 (.58mm) for leads number 1, 7, 8 and 14 only.
- 3. Dimension "Q" shall be measured from the seating plane to the base plane.
- 4. This dimension allows for off-center lid, meniscus and glass overrun.
- The basic pin spacing is .100 (2.54mm) between centerlines. Each pin centerline shall be located within ±.010 (.25mm) of its exact longitudinal position relative to pins 1 and 14.
- 6. Applies to all four corners (leads number 1, 7, 8, and 14).
- 7. "eA" shall be measured at the center of the lead bends or at the centerline of the leads when " $\alpha$ " is 90°.
- 8. All leads Increase maximum limit by .003 (.08mm) measured at the center of the flat, when lead finish applied.
- 9. Twelve spaces.







### **Ordering Information**

Part Number	Package	Operating Temperature Range
LM148D	14-Lead Ceramic DIP	-55°C to +125°C
LM148D/883B	14-Lead Ceramic DIP	-55°C to +125°C

Note:

1. 883B suffix denotes Mil-Std-883, Level B processing

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